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TSM4800N15CX6

Taiwan Semiconductor

N-Channel Power MOSFET

150V, 1.4A, 480mΩ

FEATURES

- Low R_{DS(ON)} to minimize conductive losses
- Low gate charge for fast power switching
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

| KEY PERFORMANCE PARAMETERS | | | | |
|----------------------------|----------------|-------|------|--|
| PARAMETER | | VALUE | UNIT | |
| V _{DS} | | 150 | V | |
| R _{DS(on)} (max) | $V_{GS} = 10V$ | 480 | | |
| | $V_{GS} = 6V$ | 520 | mΩ | |
| Q_{g} | | 8 | nC | |

APPLICATIONS

- Battery Management System
- LED Lighting







1256

Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

| ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted) | | | | | |
|---|---------------------------------|-----------------------------------|--------------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | | V _{DS} | 150 | V | |
| Gate-Source Voltage | | V _{GS} | ±20 | V | |
| Continuous Drain Current (Note 1) | $T_{\rm C} = 25^{\circ}{\rm C}$ | | 1.4 | ^ | |
| | $T_A = 25^{\circ}C$ | Ι _D | 1.1 | - A | |
| Pulsed Drain Current | | I _{DM} | 5.6 | А | |
| Total Dower Dissipation | $T_{\rm C} = 25^{\circ}{\rm C}$ | D | 2.1 | w | |
| Total Power Dissipation | T _C = 125°C | P _D | 0.4 | vv | |
| Total Power Dissipation | T _A = 25°C | | 1.5 | 14/ | |
| | T _A = 125°C | P _D | 0.3 | W | |
| Operating Junction and Storage Temp | erature Range | T _J , T _{STG} | - 55 to +150 | °C | |

| THERMAL PERFORMANCE | | | | | |
|--|------------------|-------|------|--|--|
| PARAMETER | SYMBOL | LIMIT | UNIT | | |
| Junction to Case Thermal Resistance | R _{eJC} | 59 | °C/W | | |
| Junction to Ambient Thermal Resistance | R _{eja} | 83 | °C/W | | |

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design.

TSM4800N15CX6 Taiwan Semiconductor



| ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted) | | | | | | |
|--|--|--|-----|------|------|-------|
| PARAMETER | CONDITIONS | SYMBOL | MIN | ТҮР | MAX | UNIT |
| Static | | | | | | • |
| Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_{D} = 250 \mu A$ | BV _{DSS} | 150 | | | V |
| Gate Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250 \mu A$ | V _{GS(TH)} | 2 | 2.9 | 3.5 | V |
| Gate Threshold Voltage Temperature Coefficient | I _D = 250μA | $\frac{\Delta V_{GS(TH)}}{\Delta T_J}$ | | -6.4 | | mV/°C |
| Gate-Source Leakage Current | $V_{GS} = \pm 20V, V_{DS} = 0V$ | I _{GSS} | | | ±100 | nA |
| | $V_{GS} = 0V, V_{DS} = 150V$ | | | | 1 | μΑ |
| Drain-Source Leakage Current | V _{GS} = 0V, V _{DS} = 150V T _J = 125°C | I _{DSS} | | | 100 | |
| Drain-Source On-State Resistance | $V_{GS} = 10V, I_{D} = 1.1A$ | | | 392 | 480 | mΩ |
| (Note 2) | $V_{GS} = 6V, I_D = 1.1A$ | R _{DS(on)} | | 428 | 520 | |
| Forward Transconductance (Note 2) | $V_{\text{DS}}=5V,\ I_{\text{D}}=1.1A$ | g _{fs} | | 3.3 | | S |
| Dynamic ^(Note 3) | | | | | | |
| Total Gate Charge | $V_{GS} = 10V, V_{DS} = 10V,$ $I_{D} = 1.1A$ | Qg | | 8 | | |
| Total Gate Charge | | Qg | | 5 | | nC |
| Gate-Source Charge | $V_{GS} = 6V, V_{DS} = 10V,$ $I_{D} = 1.1A$ | Q _{gs} | | 2 | | |
| Gate-Drain Charge | $I_D = 1.1A$ | Q_{gd} | | 2.7 | | |
| Input Capacitance | | C _{iss} | | 332 | | |
| Output Capacitance | $V_{GS} = 0V, V_{DS} = 10V$ f = 1.0MHz | C _{oss} | | 20 | | pF |
| Reverse Transfer Capacitance | | C _{rss} | | 1 | | |
| Gate Resistance | f = 1.0MHz | R _g | | 3.5 | | Ω |
| Switching (Note 3) | | | | | | |
| Turn-On Delay Time | | t _{d(on)} | | 5 | | |
| Turn-On Rise Time | $V_{GS} = 10V, V_{DS} = 10V,$ | t _r | | 18 | | |
| Turn-Off Delay Time | $I_{\rm D} = 1.1 {\rm A}, {\rm R}_{\rm G} = 2 {\Omega},$ | t _{d(off)} | | 9 | | ns |
| Turn-Off Fall Time | | t _f | | 18 | | |
| Source-Drain Diode | | | | | | |
| Forward Voltage (Note 2) | $V_{GS} = 0V, I_{S} = 1.1A$ | V_{SD} | | | 1.2 | V |
| Reverse Recovery Time | I _S = 1.1A , | t _{rr} | | 51 | | ns |
| Reverse Recovery Charge | dl/dt = 100A/µs | Q _{rr} | | 59 | | nC |

Notes:

1. Silicon limited current only.

2. Pulse test: Pulse Width \leq 300µs, duty cycle \leq 2%.

3. Switching time is essentially independent of operating temperature.

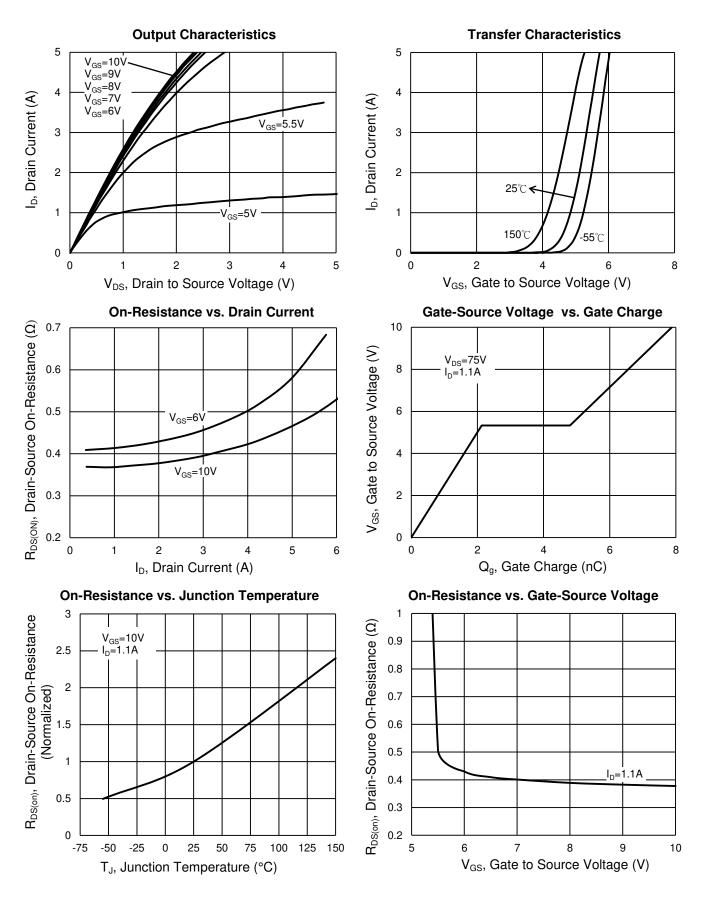
ORDERING INFORMATION

| PART NO. | PACKAGE | PACKING |
|-------------------|---------|--------------------|
| TSM4800N15CX6 RFG | SOT-26 | 3,000pcs / 7" Reel |



CHARACTERISTICS CURVES

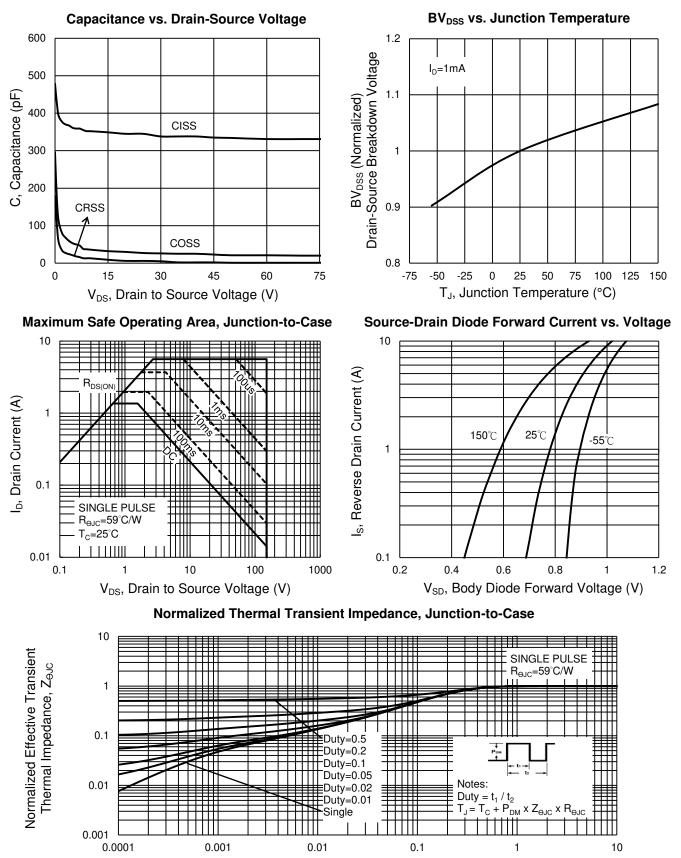
(T_A = 25°C unless otherwise noted)





CHARACTERISTICS CURVES

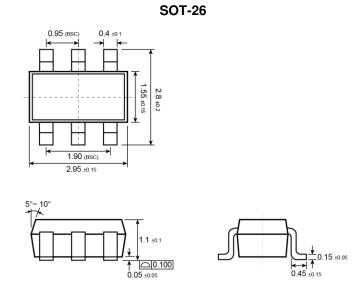
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$



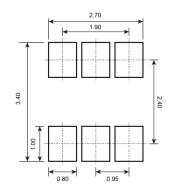
t, Square Wave Pulse Duration (sec)



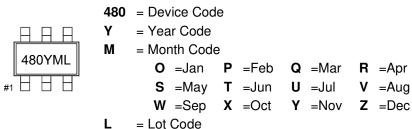
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



= Lot Code

Version: A1704



TSM4800N15CX6

Taiwan Semiconductor

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